KEY PARAMETERS

 V_{RRM}

I_{F(AV)}

I_{FSM}

DS4219-2.3

3500V

2135A

20000A

1500μC

6.5μ**s**

DFB54FAST RECOVERY DIODE

APPLICATIONS

- Power Supplies.
- Freewheel Diode.
- Battery Chargers.
- D.C. Motor Control.
- Welding.
- Rectification.

FEATURES

- Double Side Cooling.
- High Surge Capability.
- Low Recovery Charge.

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V	Conditions
DFB54 35	3500	$V_{RSM} = V_{RRM} + 100V$
DFB54 34	3400	IXOW IXIXW
DFB54 33	3300	
DFB54 32	3200	
DFB54 31	3100	
DFB54 30	3000	

Lower voltage grades available.

Outline type code: DO200AD. See package outlines for further information.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units			
Double Side Cooled							
I _{F(AV)}	Mean forward current	Half wave resistive load, T _{case} = 65°C	2135	Α			
I _{F(RMS)}	RMS value	$T_{case} = 65^{\circ}C$	3350	Α			
I _F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	3060	Α			
Single Side Cooled (Anode side)							
I _{F(AV)}	Mean forward current	Half wave resistive load, T _{case} = 65°C	1320	А			
I _{F(RMS)}	RMS value	T _{case} = 65°C	2080	А			
I _F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	1810	А			

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SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{FSM}	Surge (non-repetitive) forward current	10ma half aine: with 09/ \/ T = 1500C	20.0	kA
l ² t	I ² t for fusing	10ms half sine; with 0% V _{RRM,} T _j = 150°C	2000 x 10 ³	A ² s
I _{FSM}	Surge (non-repetitive) forward current	10mg half ging; with 50% \ T = 150%	16	kA
l²t	I ² t for fusing	10ms half sine; with 50% V_{RRM} , $T_j = 150$ °C	1280 x 10 ³	A ² s

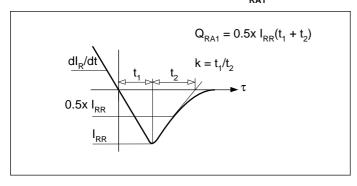
THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
	Thermal resistance - junction to case	Double side cooled	dc	-	0.013	°C/W
R _{th(j-c)}		Single side cooled	Anode dc	-	0.025	°C/W
			Cathode dc	-	0.027	°C/W
R _{th(c-h)}	Thermal resistance - case to heatsink	Clamping force 44kN with mounting compound	Double side	-	0.003	°C/W
			Single side	-	0.006	°C/W
T _{vj}	Virtual junction temperature	Forward (conducting)		-	150	°C
T _{stg}	Storage temperature range			-55	150	°C
-	Clamping force			39.6	48.4	kN

CHARACTERISTICS

Symbol	Parameter	Conditions	Тур.	Max.	Units
V _{FM}	Forward voltage	At 1500A peak, T _{case} = 25°C	-	1.7	V
I _{RRM}	Peak reverse current	At V _{RRM} , T _{case} = 150°C	-	100	mA
t _{rr}	Reverse recovery time		-	6.5	μs
Q _{RA1}	Recovered charge (50% chord)	$I_F = 1000A$, $di_{RR}/dt = 100A/\mu s$	-	1500	μC
I _{RM}	Reverse recovery current	$T_{case} = 150$ °C, $V_{R} = 100$ V	-	450	Α
К	Soft factor		-	-	-
V _{TO}	Threshold voltage	At T _{vj} = 150°C	-	1.15	V
r _T	Slope resistance	At T _{vj} = 150°C	-	0.32	mΩ
V _{FRM}	Forward recovery voltage	di/dt = 1000A/μs, T _j = 125°C	-	-	V

DEFINITION OF K FACTOR AND \mathbf{Q}_{RA1}



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CURVES

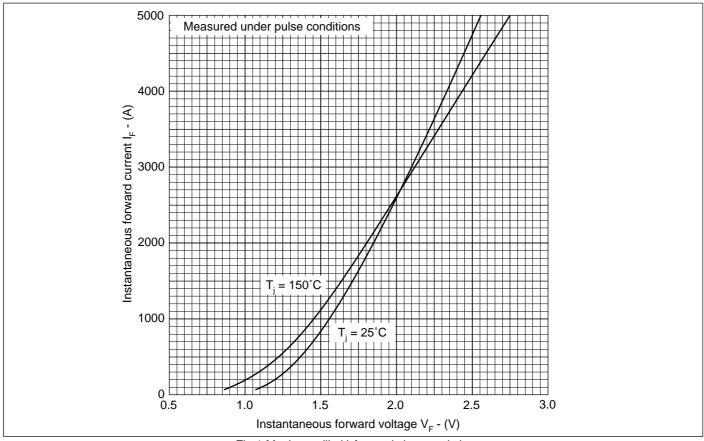


Fig.1 Maximum (limit) forward characteristics

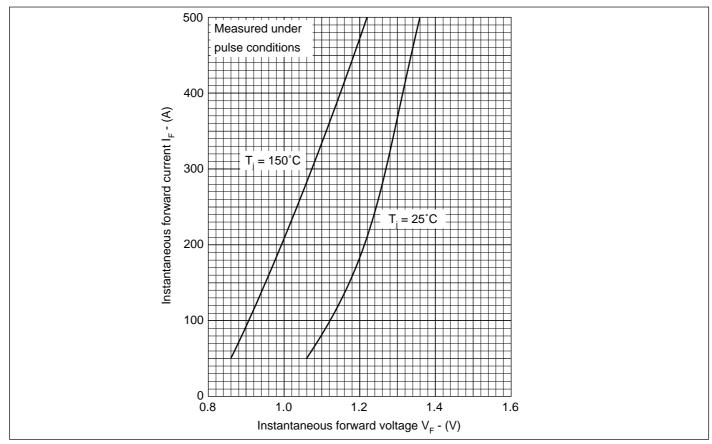


Fig.2 Maximum (limit) forward characteristics

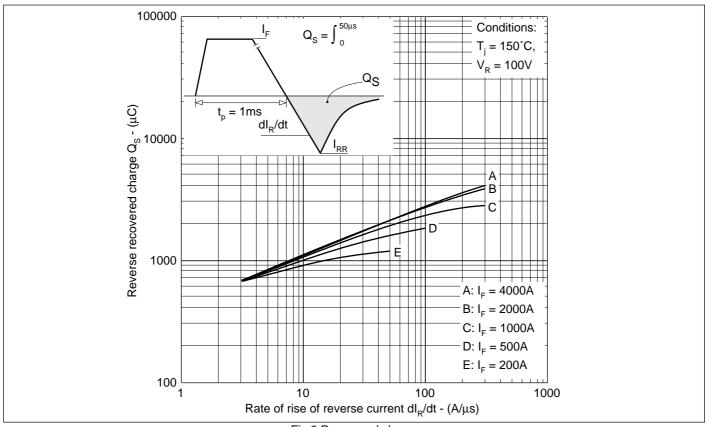


Fig.3 Recovered charge

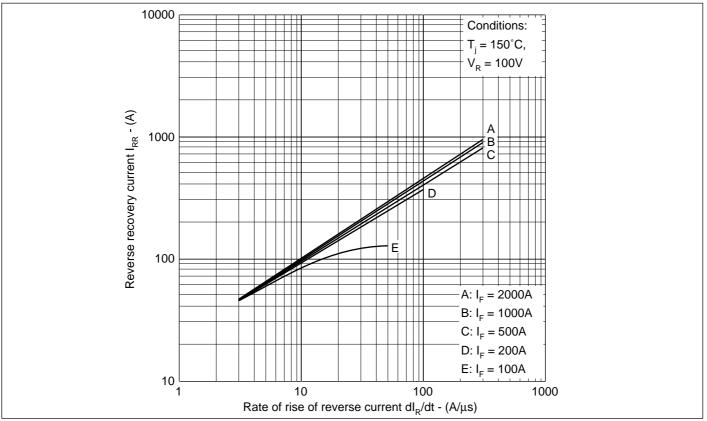


Fig.4 Typical reverse recovery current vs rate of rise of reverse current

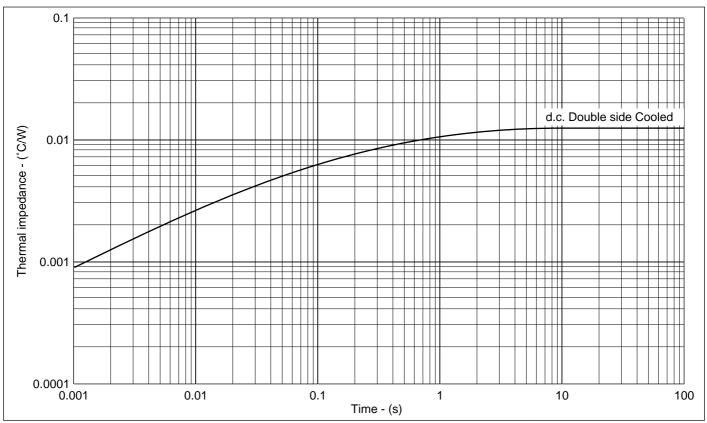
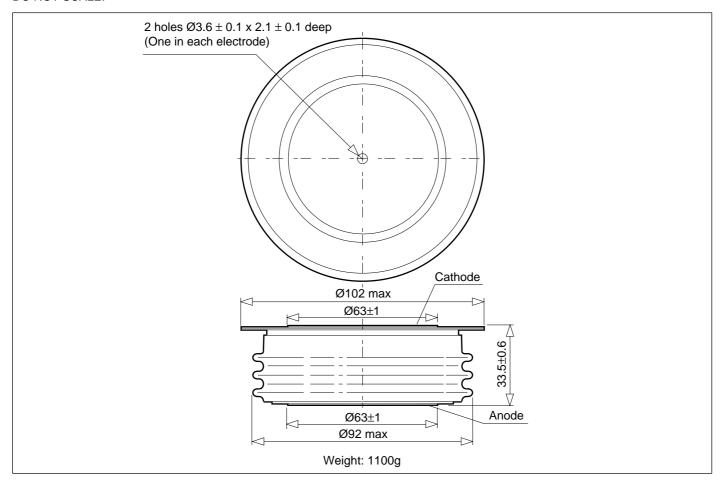


Fig.5 Maximum (limit) transient thermal impedance - junction to case - (°C/W)

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PACKAGE DETAILS - DO200AD

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





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